

Silicon Controlled Rectifiers Reverse Blocking Triode Thyristors

... multi-purpose PNP silicon controlled rectifiers suited for industrial, consumer, and military applications. Offered in a choice of space-saving, economical packages for mounting versatility.

- Uniform Low-Level Noise-immune Gate Triggering — $I_{GT} = 10 \text{ mA (Typ) @ } T_C = 25^\circ\text{C}$
- Low Forward "On" Voltage — $V_T = 1 \text{ V (Typ) @ 5 Amp @ } 25^\circ\text{C}$
- High Surge-Current Capability — $I_{TSM} = 100 \text{ Amp Peak}$
- Shorted Emitter Construction

MAXIMUM RATINGS (Apply over operating temperature range and for all case types unless otherwise noted.)

Rating	Symbol	Value	Unit
*Peak Repetitive Forward and Reverse Blocking Voltage, Note 1 2N4168, 84, 2N4188, 86, 2N4170, 88, 2N4172, 88, 2N4174, 90	V_{ORM} or V_{RRM}	50 100 200 400 800	Volts
Forward Current RMS	$I_T(\text{RMS})$	8	Amps
*Peak Forward Surge Current (One cycle, 60 Hz, $T_J = -40 \text{ to } +100^\circ\text{C}$)	I_{TSM}	100	Amps
Circuit Fusing ($t = 8.3 \text{ ms}$)	I_2t	40	A^2s
*Peak Gate Power	PGM	6	Watts
*Average Gate Power	$PG(\text{AV})$	0.5	Watt
*Peak Gate Current	I_{GM}	2	Amps
Peak Gate Voltage, Note 2	V_{GM}	10	Volts
*Operating Temperature Range	T_J	-40 to +100	$^\circ\text{C}$
*Storage Temperature Range	T_{stg}	-40 to +150	$^\circ\text{C}$
Stud Torque		15	in. lb.

**2N4168
thru
2N4174
2N4184
thru
2N4190**

**SCRs
8 AMPERES RMS
60 thru 800 VOLTS**



CASE 88-01

2N4168 thru 2N4174



CASE 87L-02

2N4184 thru 2N4190



THERMAL CHARACTERISTICS

Characteristic	Symbol	Typ	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.5	2.5*	$^{\circ}C/W$
Thermal Resistance, Case to Ambient (See Figure 11) 2N4183-98	$R_{\theta CA}$	50	—	$^{\circ}C/W$

*Indicates JEDEC Registered Data.

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
*Peak Forward or Reverse Blocking Current (Rated V_{DRM} or V_{RRM} , gate open) $T_C = 25^{\circ}C$ $T_C = 100^{\circ}C$	I_{ORM}, I_{RRM}	— —	— —	10 2	μA mA
Gate Trigger Current (Continuous dc), Note 1 ($V_D = 7 V_{dc}, R_L = 100 \Omega$) *($V_D = 7 V_{dc}, R_L = 100 \Omega, T_C = -40^{\circ}C$)	I_{GT}	— —	10 —	30 60	mA
Gate Trigger Voltage (Continuous dc) ($V_D = 7 V_{dc}, R_L = 100 \Omega$) *($V_D = 7 V_{dc}, R_L = 100 \Omega, T_C = -40^{\circ}C$) *($V_D = 7 V_{dc}, R_L = 100 \Omega, T_C = 100^{\circ}C$)	V_{GT}	— — 0.2	0.75 — —	1.5 2.5 —	Volts
*Forward "On" Voltage (pulsed, 1 ms max, duty cycle $\leq 1\%$) ($I_{TM} = 15.7 A$)	V_{TM}	—	1.4	2	Volts
Holding Current ($V_D = 7 V_{dc}$, gate open) *($V_D = 7 V_{dc}$, gate open, $T_C = -40^{\circ}C$)	I_H	— —	10 —	30 60	mA
Turn-On Time ($t_d + t_r$) ($I_G = 20 mA_{dc}, I_F = 5 A_{dc}, V_D = \text{Rated } V_{DRM}$)	t_{on}	—	1	—	μs
Turn-Off Time ($I_F = 5 A_{dc}, I_R = 5 A_{dc}$) ($I_F = 5 A_{dc}, I_R = 5 A_{dc}, T_C = 100^{\circ}C, V_D = \text{Rated } V_{DRM}$) ($dv/dt = 30 V/\mu s$)	t_{off}	— —	15 25	— —	μs
Forward Voltage Application Rate (Exponential) (Gate open, $T_C = 100^{\circ}C, V_D = \text{Rated } V_{DRM}$)	dv/dt	—	50	—	$V/\mu s$